Unitized Semiconductor Devices - Page 1 of 1



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Inclosure Material:

Plastic

Overall Length:

Between 2.8 millimeters and 3.0 millimeters

Overall Height:

1.1 millimeters

Overall Width:

Between 1.5 millimeters and 1.7 millimeters

End Application:

Ca70608-0019191560, receiver-transmitter

Joint Electronic Device Engineering Council/jedec/case Outline Designation:

Mo-193, var. Aa, issue c, dated january 2000

Component Name And Quantity:

2 transistor

Mounting Method:

Press fit

Semiconductor Material:

Silicon all transistor

Voltage Rating In Volts Per Characteristic:

30.0 collector to emitter voltage, dc all transistor and 60.0 collector to base voltage, dc all transistor and 5.0 emitter to base voltage, dc all transistor

Current Rating Per Characteristic:

500.00 milliamperes collector current, dc all transistor

Power Rating Per Characteristic:

700.0 milliwatts total power dissipation all transistor

Product Name:

Dwg - cage 19156: transistor array, general purpose amplifier; datasheet - cage 7d893: npn and pnp general purpose amplifier

Special Features:

Case: super sot-6; transistor type: c1, b1, e1: npn; c2, b2, e2: pnp; operating and storage junction temp range: -55.0 to +150.0 degrees c

Terminal Type And Quantity:

6 tab, solder lug

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

Yes - demil/mli

Fiig:

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